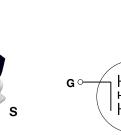
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BSS84 Rev. C1 / BSS110. Rev. A2

Symbol	Parameter	BSS84	BSS110	Units	
V <sub>DSS</sub>	Drain-Source Voltage	-50		V	
$V_{\text{DGR}}$	Drain-Gate Voltage ( $R_{GS} \le 20 \text{ K}\Omega$ )	-50		V	
$V_{GSS}$	Gate-Source Voltage - Continuous	±20		V	
$I_{D} \qquad Drain Current - Continuous @ T_{A} = 30/35^{\circ}C$ $- Pulsed \qquad @ T_{A} = 25^{\circ}C$		-0.13	-0.17	А	
		-0.52	-0.52 -0.68		
P <sub>D</sub>	Maximum Power Dissipation $T_A = 25^{\circ}C$	0.36	0.36 0.63		
T_,,T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to 150		°C	
TL	Maximum lead temperature for soldering purposes, 1/16" from case for 10 seconds	300			
THERMA	L CHARACTERISTICS			•	
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	350	200	°C/W	

	2	
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# BSS84 / BSS110 P-Channel Enhancement Mode Field Effect Transistor

FAIRCHILD

## **General Description**

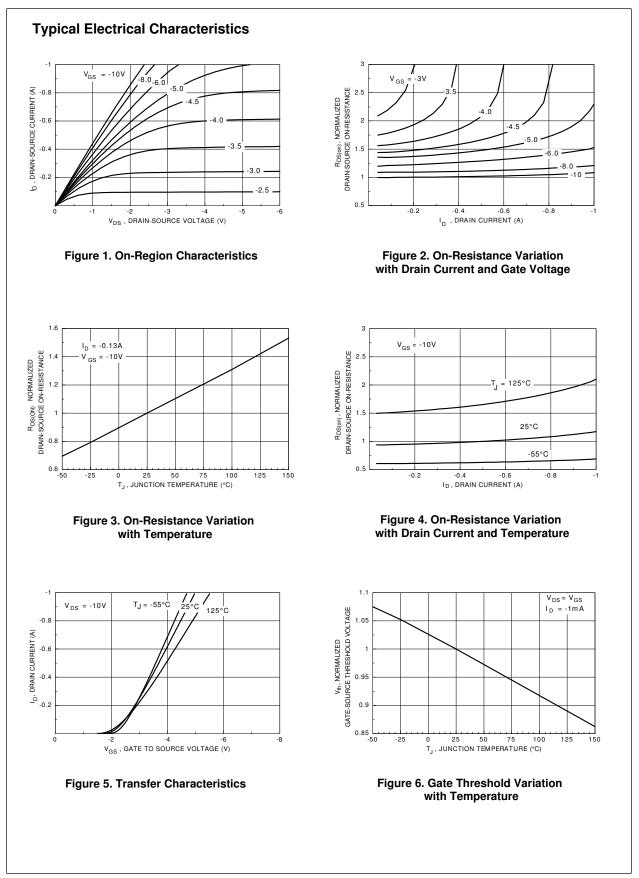
These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is designed to minimize on-state resistance, provide rugged and reliable performance and fast switching. They can be used, with a minimum of effort, in most applications requiring up to 0.17A DC and can deliver pulsed currents up to 0.68A. This product is particularly suited to low voltage applications requiring a low current high side switch.

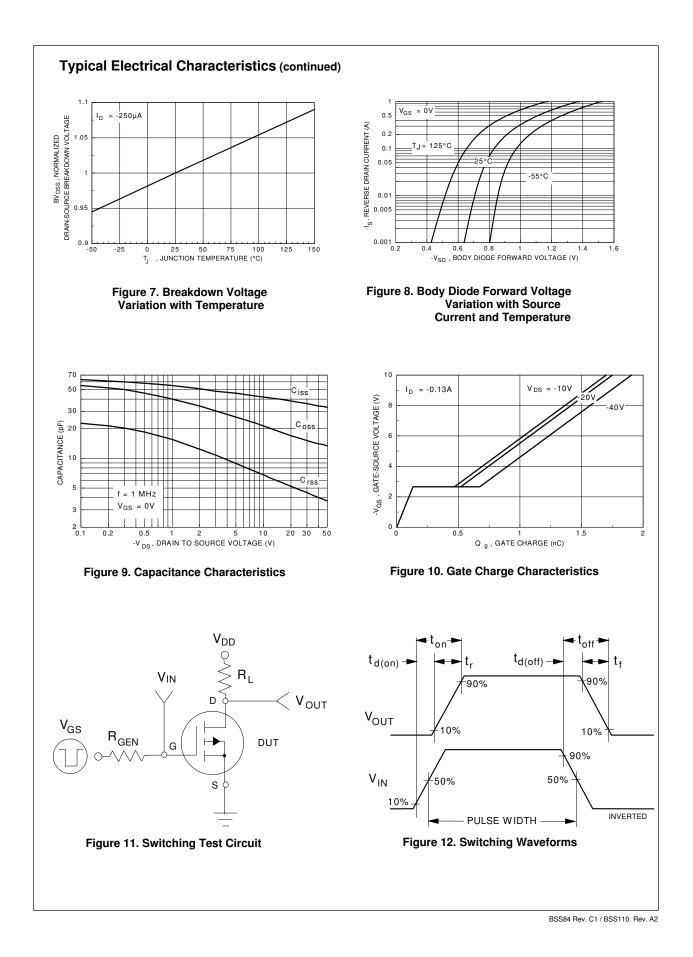
# Features

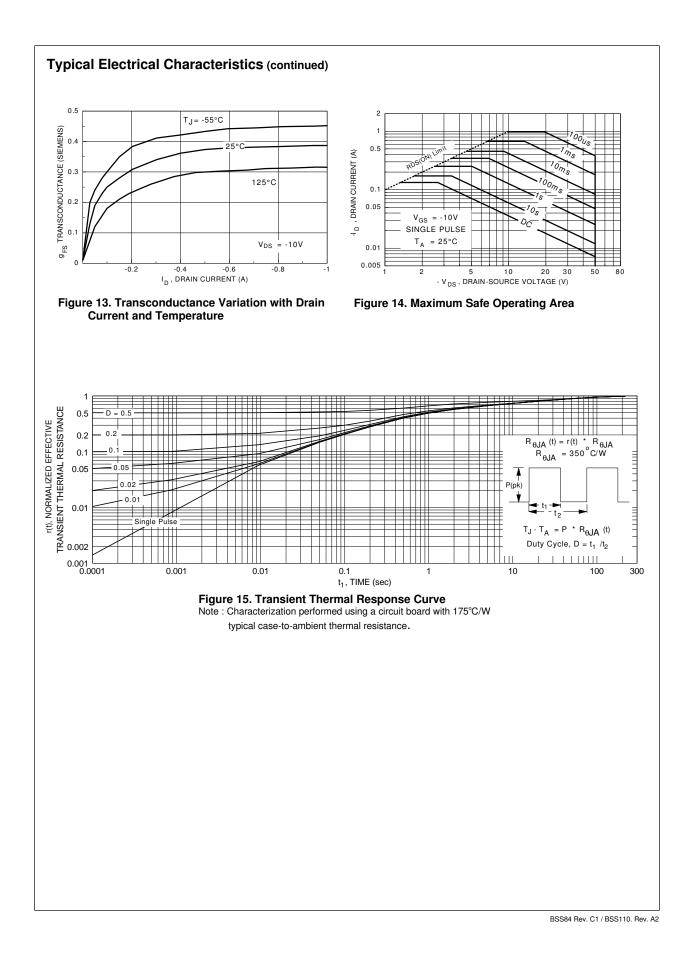
- BSS84: -0.13A, -50V. R<sub>DS(ON)</sub> = 10Ω @ V<sub>GS</sub> = -5V.
  BSS110: -0.17A, -50V. R<sub>DS(ON)</sub> = 10Ω @ V<sub>GS</sub> = -10V
- Voltage controlled p-channel small signal switch.
- High density cell design for low R<sub>DS(ON)</sub>.
- High saturation current.

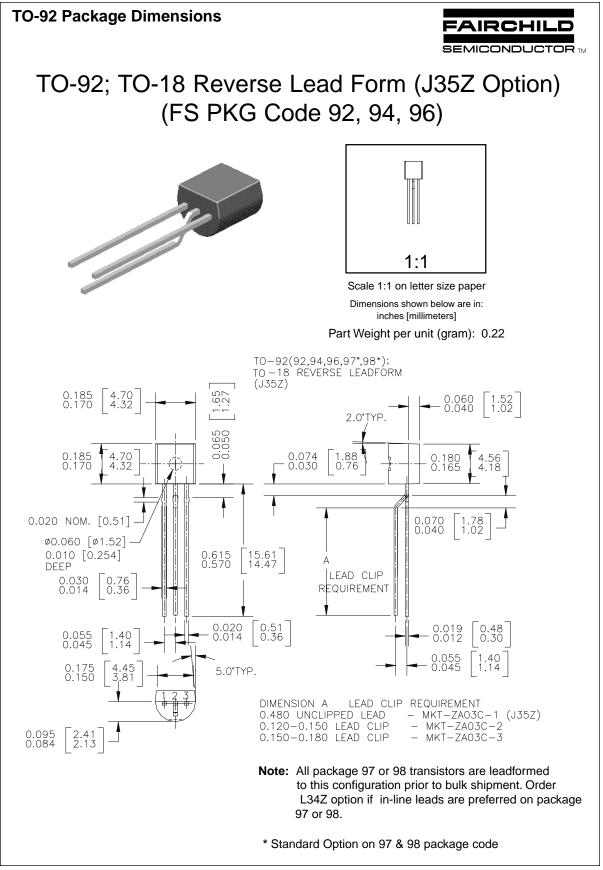
May 1999

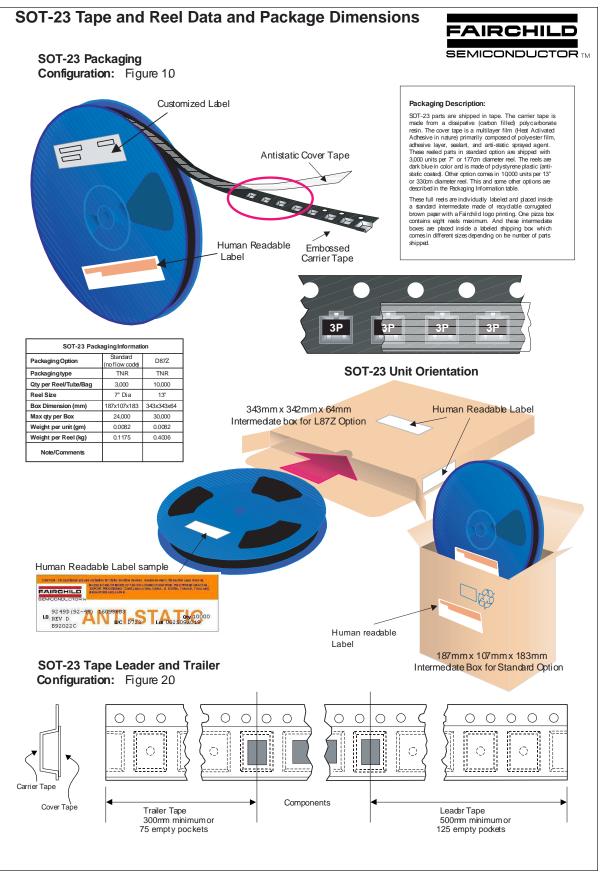
Symbol	Parameter	Conditions		Туре	Min	Тур	Max	Units	
OFF CHA	RACTERISTICS								
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		All	-50			V	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -50 V,$		All			-15	μA	
		$V_{GS} = 0 V$ $T_{J} = 125$	Tյ= 125°C				-60	μA	
		$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}$					-0.1	μA	
	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$		All			-10	nA	
ON CHA	RACTERISTICS (Note 1)	·							
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -1 \text{ mA}$		All	-0.8	-1.75	-2	V	
	Static Drain-Source On-Resistance	$V_{GS} = -5V, I_{D} = -0.10 \text{ A}$		BSS84		3.2	10	Ω	
		$V_{GS} = -10 \text{ V}, \ \text{I}_{D} = -0.17 \text{ A}$		BSS110		2.2	10		
g <sub>FS</sub> Forward Transco	Forward Transconductance	$V_{DS} = -25 \text{ V}, I_{D} = -0.10 \text{ A}$		BSS84	0.05	0.27	27 S		
		$V_{\rm DS} = -10 \text{ V}, \text{ I}_{\rm D} = -0.17 \text{ A}$		BSS110	0.05	0.29			
DYNAMIC	CHARACTERISTICS								
C <sub>iss</sub> Input Capacitance	Input Capacitance	$V_{DS} = -25 V, V_{GS} = 0 V,$ f = 1.0 MHz	BSS84		37	45	pF		
				BSS110		37	40		
C <sub>oss</sub>	Output Capacitance			All		16	25	рF	
C <sub>rss</sub>	Reverse Transfer Capacitance			All		5	12	рF	
SWITCHI	NG CHARACTERISTICS (Note 1)								
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{\text{DD}} = -30 \text{ V}, \ I_{\text{D}} = -0.27 \text{ A},$		All			12	nS	
t,	Turn - On Rise Time	$V_{\rm GS} = -10 \text{ V}, \text{ R}_{\rm GEN} = 50 \Omega$		All			50	nS	
t <sub>D(off)</sub>	Turn - Off Delay Time			All			10	nS	
t,	Turn - Off Fall Time	7		All			25	nS	
1	URCE DIODE CHARACTERISTICS								
I <sub>s</sub> Continuous Source Diode Current				BSS84			-0.13	Α	
3			BSS110			-0.17			
I <sub>SM</sub> Maximum Pulsed Source Diode Current		(Note 1)		BSS84			-0.52	Α	
GWI				BSS110			-0.68		
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = -0.26 A$ (Note 1)		BSS84		-0.95	-1.2	V	
		$V_{GS} = 0 \text{ V}, \text{ I}_{S} = -0.34 \text{ A}$ (Note 1)		BSS110		-1	-1.2		



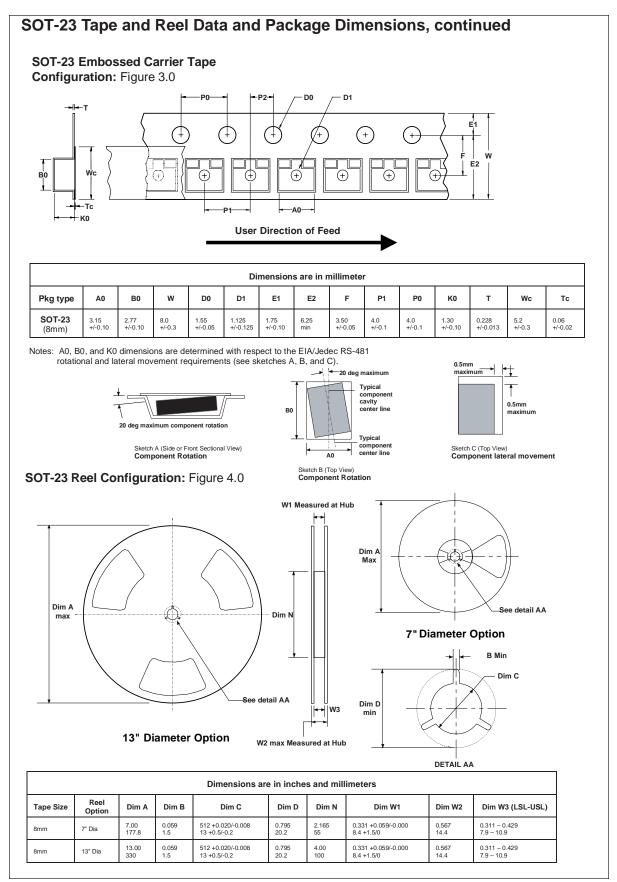




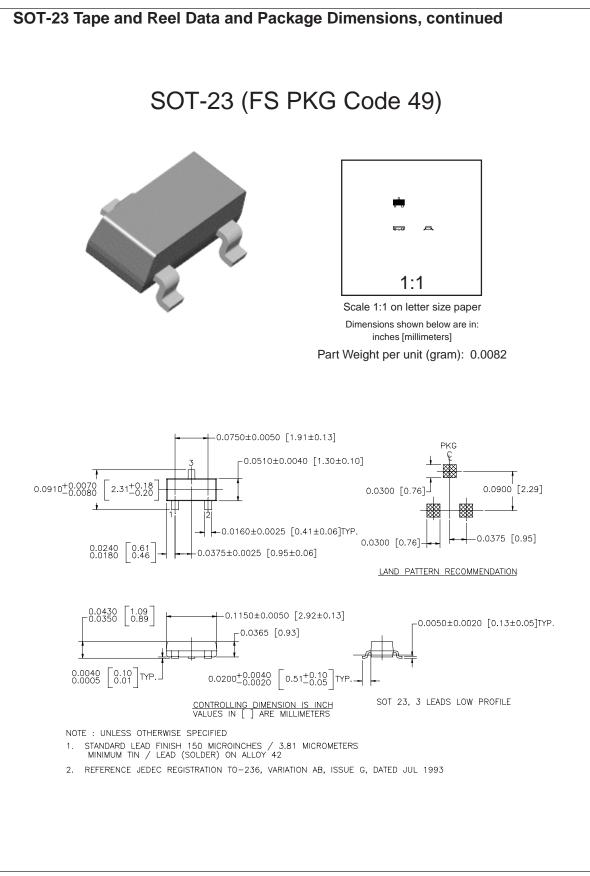




September 1999, Rev. C



September 1999, Rev. C



September 1998, Rev. A1

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**Definition of Terms** 

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